

DESCRIPTION

SiC Schottky Diode has no switching loss, provides improved system efficiency against Si diodes by utilizing new semiconductor material-Silicon Carbide, enables higher operating frequency, and helps increasing power density and reduction of system size /cost. Its high reliability ensures robust operation during surge or over-voltage conditions.

FEATURES

- Max Junction Temperature 175°C
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery

MECHANICAL DATA

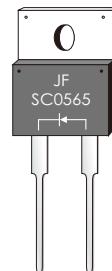
- Case: JEDEC TO-220AC/ITO-220AC/TO-263AC/TO-252
- Molding compound meets UL94V-0 flammability rating
- Terminals: Lead solderable per J-STD-002 and JESD22-B102
- Polarity: As marked
- Mounting Torque: 10 in-lbs maximum

TYPICAL APPLICATIONS

- General Purpose
- SMPS, Solar inverter, UPS
- Power Switching Circuits

TO-220AC

SC0565



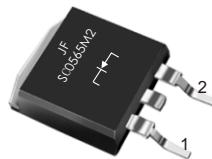
ITO-220AC

SC0565F



TO-252

SC0565M2



TO-263AC

SC0565D2



MAXIMUM RATINGS

(Ratings at 25°C ambient temperature unless otherwise specified)

Parameter	Symbol	Value	Unit
Maximum repetitive peak reverse voltage	V _{RRM}	650	V
Continuous Rectified Forward Current	I _F	5	A
Repetitive Forward Surge Current(NOTE 1)	I _{F, RM}	30	A
Operating junction temperature range	T _J	-55 to+175	°C
Storage temperature range	T _{stg}	-55 to+175	°C

Notes: 1.Half-Sine Pulse, tp=8.3ms

RATINGS AND CHARACTERISTIC

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ C$ Unless otherwise noted)

Parameter	Test Conditions		Symbol	TYP.	MAX.	Unit	
Instantaneous forward voltage	$I_F=5A$	$T_A=25^\circ C$	V_F	1. 6	1. 8	V	
		$T_A=175^\circ C$		1. 8	2. 0		
Reverse current	$V_R=650V$	$T_A=25^\circ C$	I_R	–	10	μA	
		$T_A=125^\circ C$		–	40		
		$T_A=175^\circ C$		–	100		
Typical junction capacitance	$V_R=1V, f=100kHz$		C_J	208	–	pF	
	$V_R=10V, f=100kHz$			90	–		
	$V_R=40V, f=100kHz$			45	–		

THERMAL CHARACTERISTICS ($T_A=25^\circ C$ Unless otherwise noted)

Parameter	Symbol	SC0565	SC0565F	SC0565D2	SC0565M2	Unit
Typical thermal resistance ²⁾	$R_{\theta JC}$	2.5	4.5	2.5	2.5	$^\circ C/W$

2.Thermal resistance from junction to case

RATINGS AND CHARACTERISTIC

FIG.1-FORWARD CURRENT DERATING CURVE

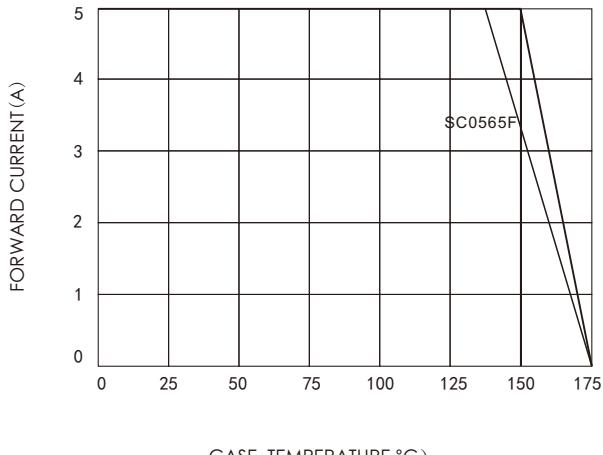


FIG.2-TYPICAL JUNCTION CAPACITANCE

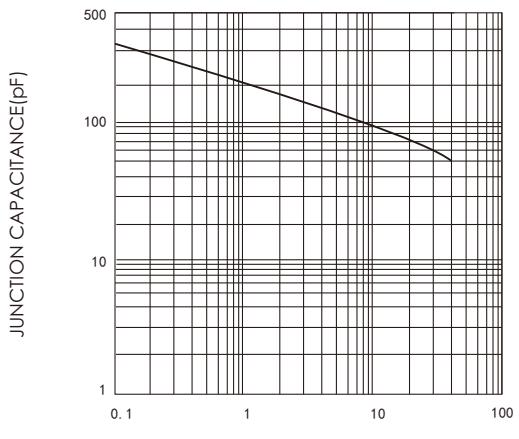


FIG.2-FORWARD CHARACTERISTICS

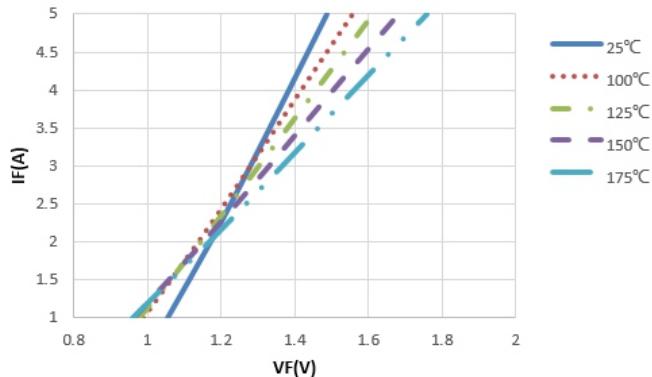
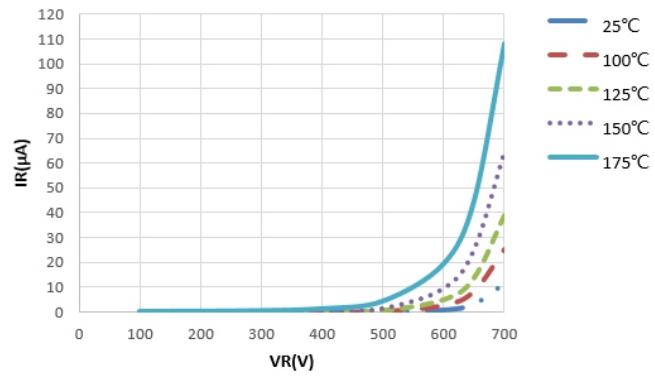
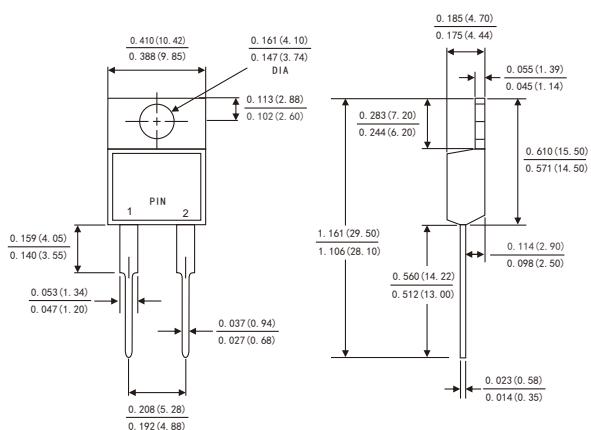


FIG.4-REVERSE CHARACTERISTICS

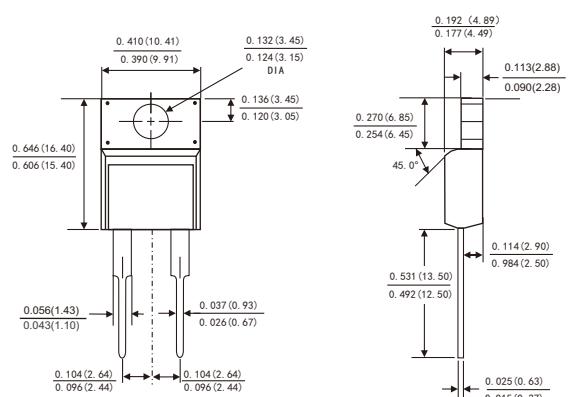


PACKAGE OUTLINE DIMENSIONS

TO-220AC



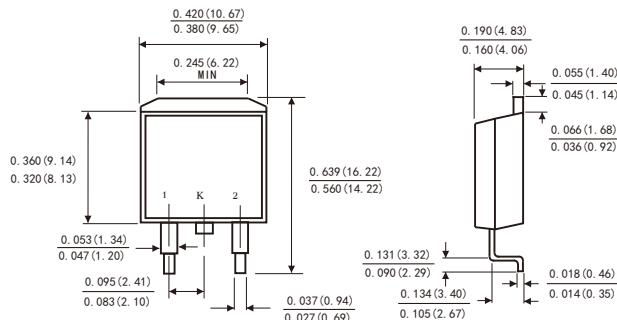
ITO-220AC



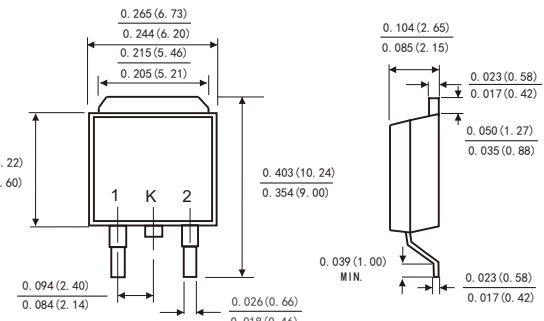
Dimensions in inches and (millimeters)

Dimensions in inches and (millimeters)

TO-263

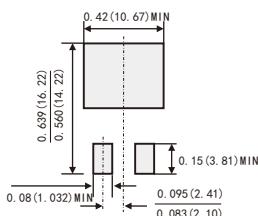


TO-252



Suggested Pad Layout

(TO-263)



Suggested Pad Layout

(TO-252)

